

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

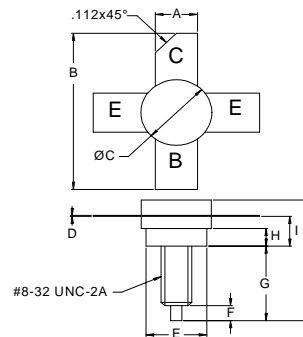
The **HF75-50S** is 50 V Class AB NPN Power transistor, designed for SSB & VHF Communacations.

FEATURES INCLUDE:

- Direct Replacement for **TH513**
- High Gain, 16 dB Typical @ 30 MHz
- Withstands Server Mismatch
- **Omnigold™** Metalization System
- 75 W P_{OUT}
- 50 V OPERATIONS

MAXIMUM RATINGS

I_C	3.25 A
V_{CB}	110 V
V_{CE}	55 V
V_{EB}	4.0 V
P_{DISS}	127 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.0 °C/W

PACKAGE STYLE .380" 4L STUD


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I _C = 100 mA	110			V
BV_{CEO}	I _C = 200 mA	55			V
BV_{EBO}	I _E = 10 mA	4.0			V
h_{FE}	V _{CE} = 6.0 V I _C = 1.4 A	19		50	---
C_{ob}	V _{CB} = 50 V f = 1.0 MHz			100	pF
G_{PE}	V _{CC} = 50 V P _{IN} = 3.0 W P _{OUT} = 75 W _{PEP}	14			dB
η_C		37			%
IMD₃	f ₁ = 30.000 MHz, f ₂ = 30.001 MHz			-30	dBc